OPA8530HN

Infrared LED Chip

High Speed / N Side-Up

GaAlAs/GaAlAs

1. Material

Substrate GaAlAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

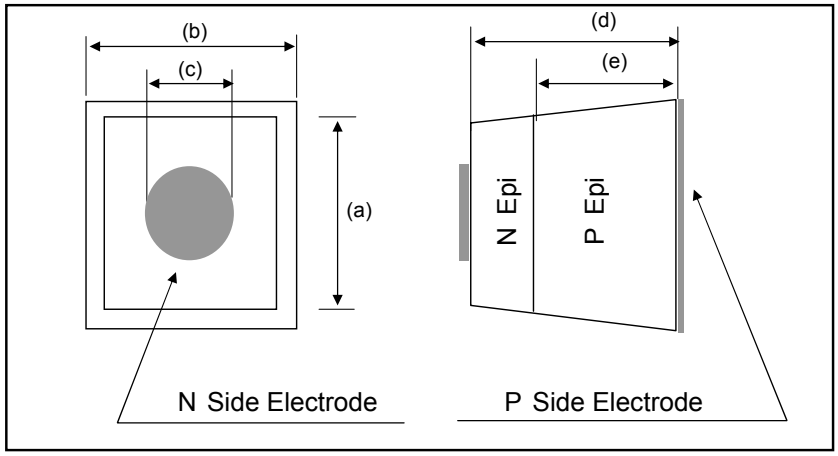
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$		1.6	1.8	V	IF=50mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O		18		mW	IF=50mA
Wavelength	λ_P		850		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	Tr		20		ns	
Fall Time	Tf		12		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area ---------- 10.8mil x 10.8mil
(b) Bottom Area ---------- 11.8mil x 11.8mil
(c) Bonding Pad ---------- 110um
(d) Chip Thickness ---------- 7mil
(e) Junction Height ---------- 5.5mil



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